

查询"2SA1242O"供应商

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

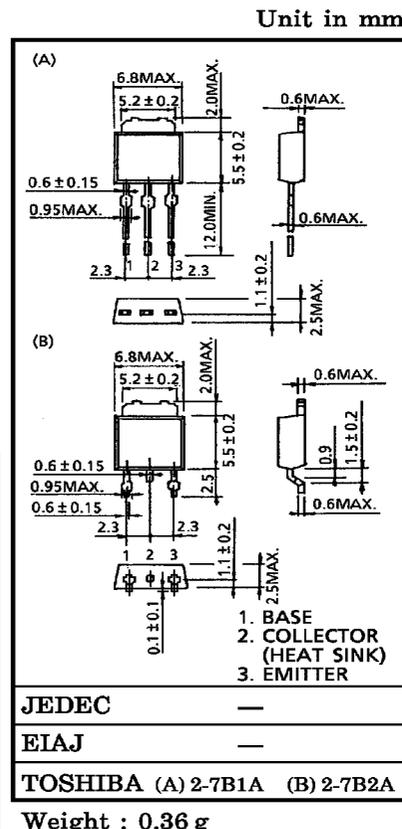
# 2SA1242

STROBE FLASH APPLICATIONS  
MEDIUM POWER AMPLIFIER APPLICATIONS

- $h_{FE} = 100\sim320$  ( $V_{CE} = -2V, I_C = -0.5A$ )
- $h_{FE} = 70$  (Min.) ( $V_{CE} = -2V, I_C = -4A$ )
- Low Collector Saturation Voltage  
:  $V_{CE(sat)} = -1.0V$  (Max.) ( $I_C = -4A, I_B = -0.1A$ )
- High Power Dissipation  
:  $P_C = 10W$  ( $T_c = 25^\circ C$ ),  $P_C = 1.0W$  ( $T_a = 25^\circ C$ )

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CB0}$	-35	V
Collector-Emitter Voltage	$V_{CE0}$	-20	V
Emitter-Base Voltage	$V_{EB0}$	-8	V
Collector Current	DC	$I_C$	-5
	Pulsed (Note 1)	$I_{CP}$	-8
Base Current	$I_B$	-0.5	A
Collector Power Dissipation	$T_a = 25^\circ C$	$P_C$	1.0
	$T_c = 25^\circ C$		10
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55~150	$^\circ C$



Note 1 : Pulse Test : Pulse width = 10 ms (Max.), Duty cycle = 30% (Max.)

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## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -35\text{ V}, I_E = 0$	—	—	-100	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = -8\text{ V}, I_C = 0$	—	—	-100	nA
Collector-Emitter Breakdown Voltage	$V_{CEO}$	$I_C = -10\text{ mA}, I_B = 0$	-20	—	—	V
Emitter-Base Breakdown Voltage	$V_{EBO}$	$I_E = -1\text{ mA}, I_C = 0$	-8	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note 2)	$V_{CE} = -2\text{ V}, I_C = -0.5\text{ A}$	100	—	320	
	$h_{FE(2)}$	$V_{CE} = -2\text{ V}, I_C = -4\text{ A}$	70	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -4\text{ A}, I_B = -0.1\text{ A}$	—	—	-1.0	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE} = -2\text{ V}, I_C = -4\text{ A}$	—	—	-1.5	V
Transition Frequency	$f_T$	$V_{CE} = -2\text{ V}, I_C = -0.5\text{ A}$	—	170	—	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10\text{ V}, I_E = 0,$ $f = 1\text{ MHz}$	—	62	—	pF

Note 2 :  $h_{FE(1)}$  Classification    O : 100~200,    Y : 160~320

